

Electrically tunable transverse magnetic focusing in graphene

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Outline

- Motivation and Introduction
- General concepts of transverse magnetic focusing (TMF)
- TMF in monolayer (MLG), bilayer (BLG) and trilayer (TLG) graphene
- TMF as a ballistic electron spectroscopy method
- Temperature dependence of the TMF spectra
- Summary and conclusions

Motivation and Introduction

Ballistic motion of electrons over macroscopic distances



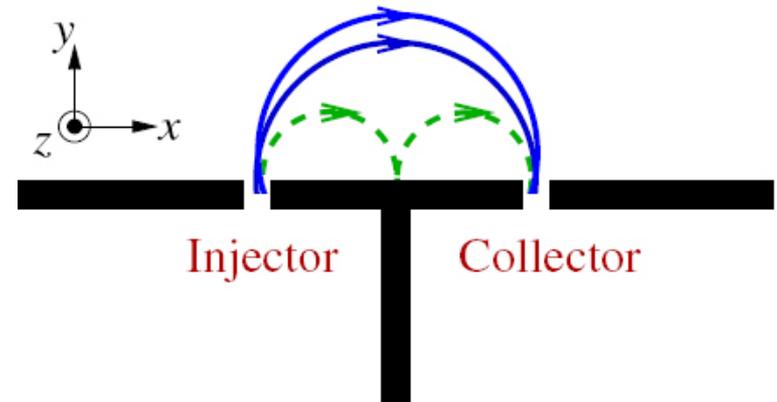
Focusing of electrons with a transverse magnetic field

TMF used to study:

- Fermi surface of metals [1]
- and semiconductor heterostructures [2]
- Andreev reflection [1]
- Spin-orbit interaction [3]
- Detection of composite fermions [4, 5]

And the quality of graphene edges:

- Exploring the graphene edges with coherent electron focusing [6]
- Boundary scattering in ballistic graphene [7]



[1] Tsoi et al., Rev. Mod. Phys. **71**, 1641 (1999)

[2] Van Houten et al., Phys. Rev. B **39**, 8556 (1989)

[3] Rokhinson et al., Phys. Rev. Lett. **93**, 146601 (2004)

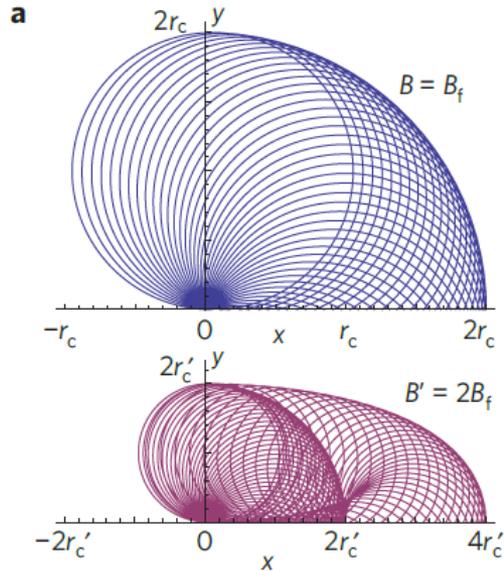
[4] Goldman et al., Phys. Rev. Lett. **72**, 2065 (1994)

[5] Smet et al., Phys. Rev. Lett. **77**, 2272 (1996)

[6] Rakyta et al., Phys. Rev. B **81**, 115411 (2010)

[7] Masubuchi et al., Phys. Rev. Lett. **109**, 036601 (2012)

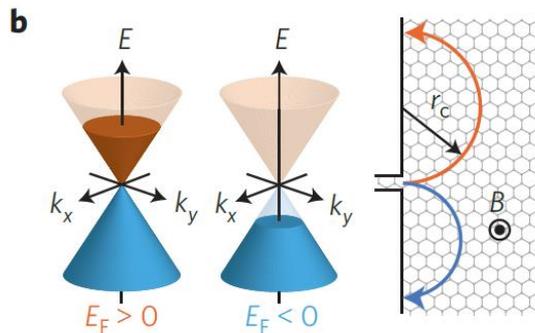
General concepts of TMF



Magnetic field B_f is required to focus electrons at a distance L :

$$B_f^{(p)} = \left(\frac{2\hbar k_F}{eL} \right) p = \left(\frac{2\hbar \sqrt{\pi n}}{eL} \right) p$$

$p-1$: # of reflections off the edge

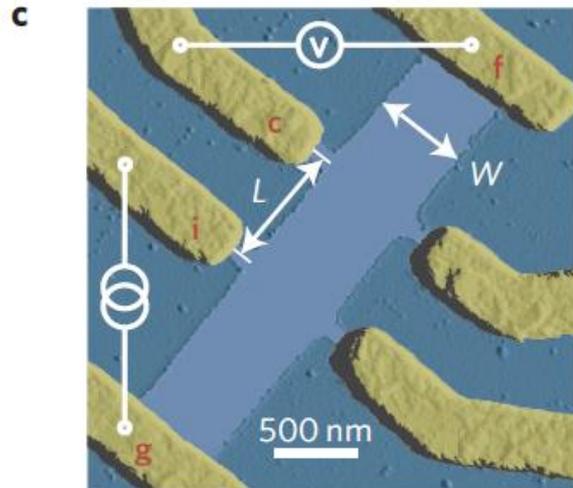


In graphene the density can be tuned continuously from the hole to the electron regime



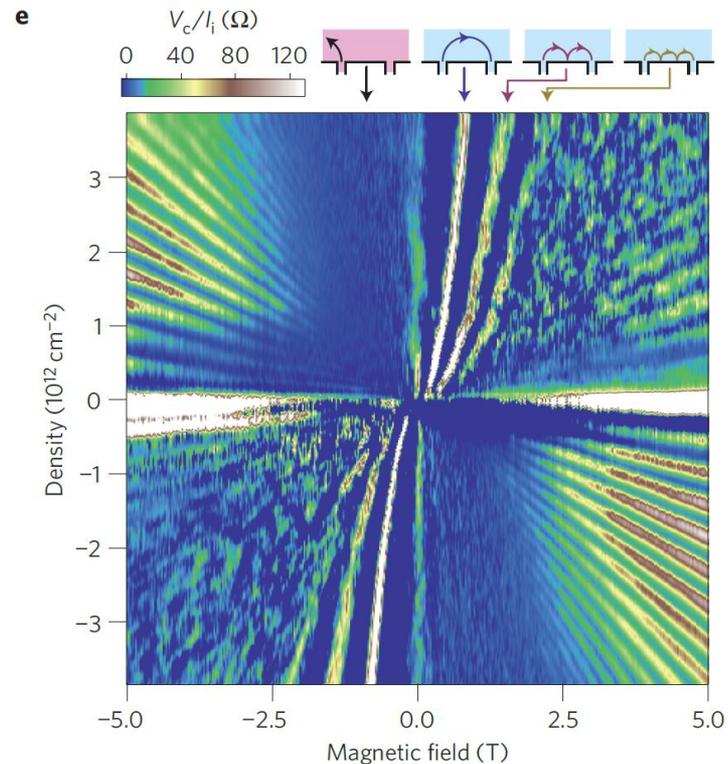
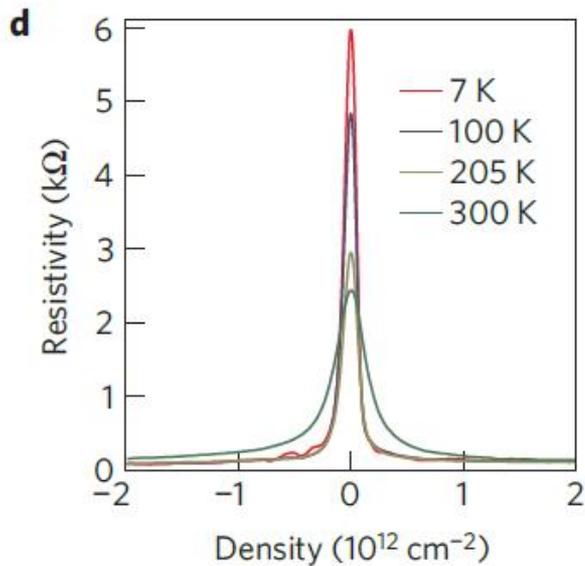
For negative density (holes) the sign of B_f changes as well!

Investigated Hall bar devices

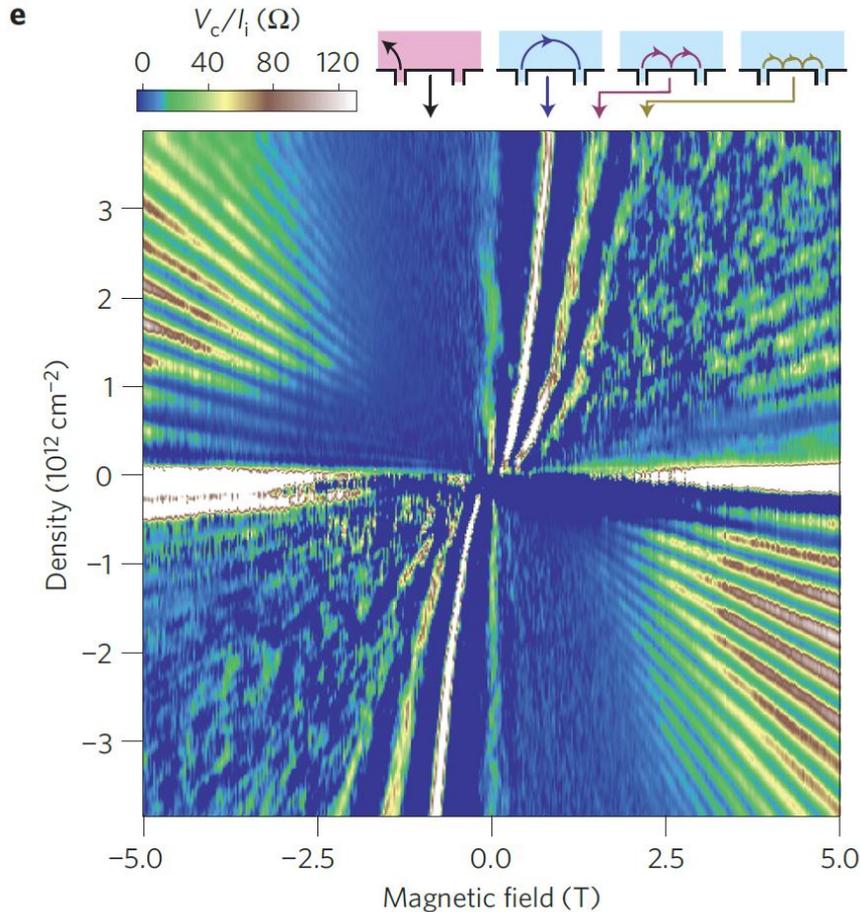


- hBN-supported MLG, BLG and TLG
- Field-effect mobility = 100'000 cm²/Vs
- mfp = 1μm

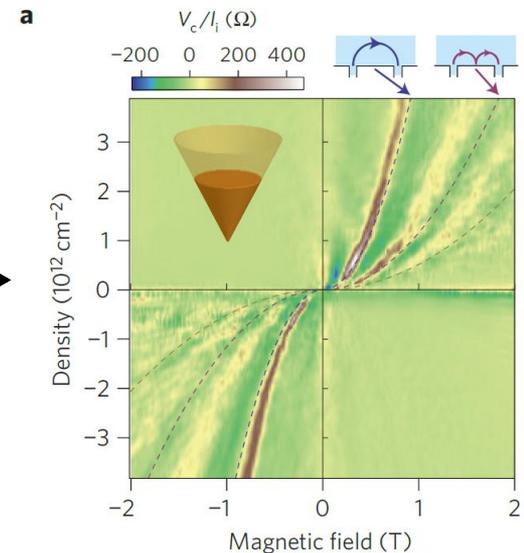
High mobility and low disorder enables TMF



TMF in monolayer graphene



- For $|B| \geq 2.5$ T SdHOs are visible
- No SdHOs in quadrants 1 and 3 due to interference of different trajectories
- For $|B| \leq 2.5$ T three unusual peaks are visible (TMF)



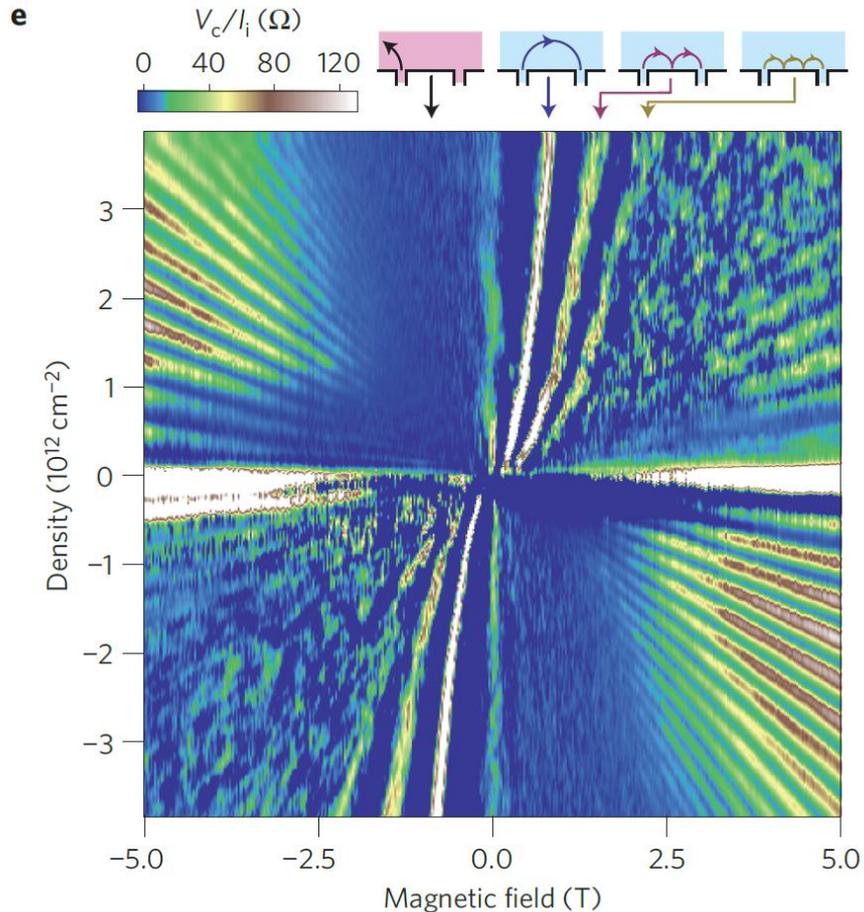
- Discrepancy between calculation and experiment
 - Finite width of injector and collector
 - Charge accumulation at the edges
 - Density fluctuations and small angle scattering

$$B_f^{(p)} = \left(\frac{2\hbar k_F}{eL} \right) p = \left(\frac{2\hbar \sqrt{\pi n}}{eL} \right) p$$

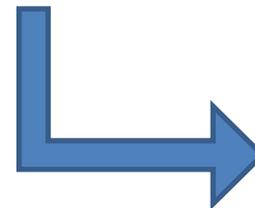
$L = 500$ nm

n known from QH

Specularity at the edge

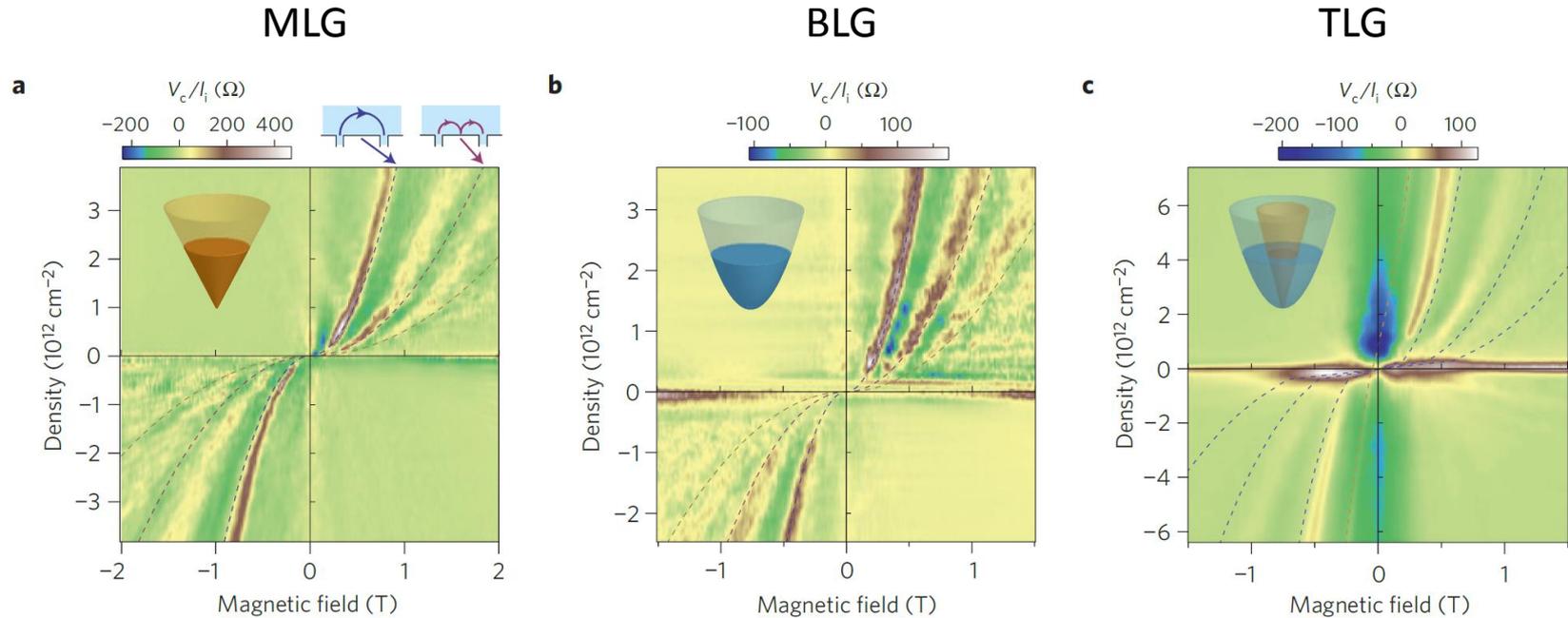


- Multiple focusing peaks observed in all investigated devices
- Significant fraction of charge carriers gets specularly reflected at the edges
- Measured specularity defined as ratio between amplitudes of second and first peaks
- For this experiment 0.2 – 0.5
- < 1 for focused-ion-beam-etched devices
- > 1 for electrostatically defined edges



Edge quality influences the specularity

TMF in MLG, BLG and TLG



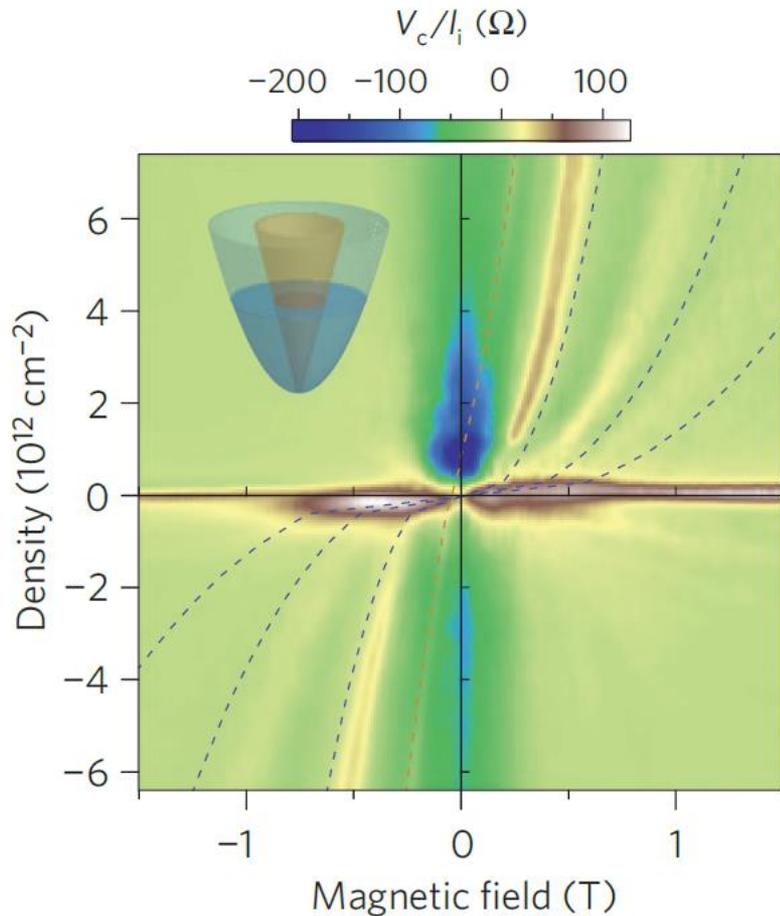
- TMF spectra very similar (despite the different band structures)
- Both have a circular Fermi surface, resulting in the same circular orbit and \sqrt{n} - dependence of k_F

TMF spectrum of TLG remarkably different
(multiband character of its band structure)



TMF as a ballistic electron spectroscopy method

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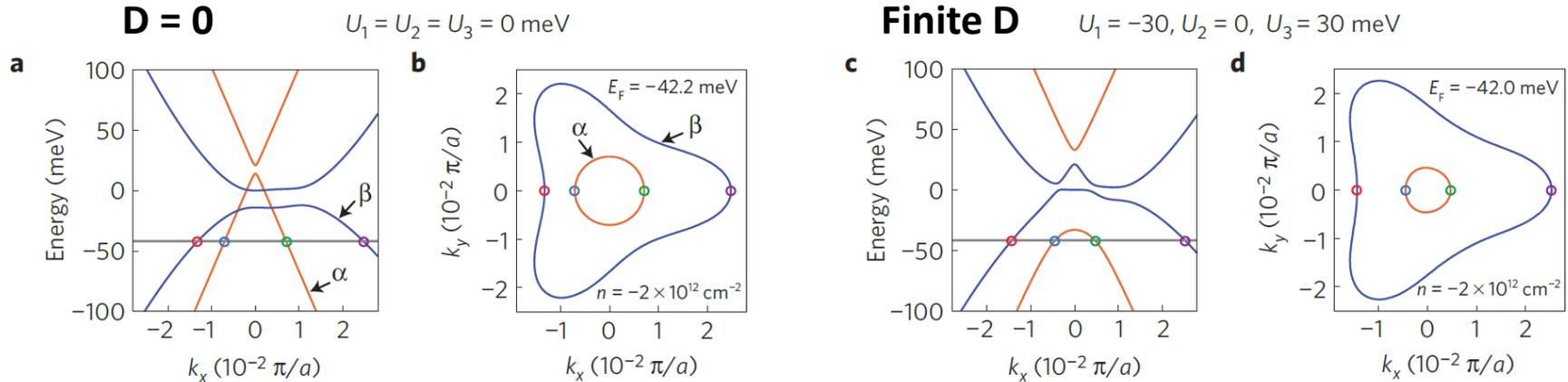


- Band structure: massless MLG-like and massive BLG-like subbands
 - Both subbands give rise to their own TMF spectra
 - No higher order peaks from MLG-like subband, masked by the stronger peaks from the BLG-like subband
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- TLG band structure can be tuned and controlled by a transverse electric displacement field D
 - TMF is sensitive to the occupation of each of the TLG subbands

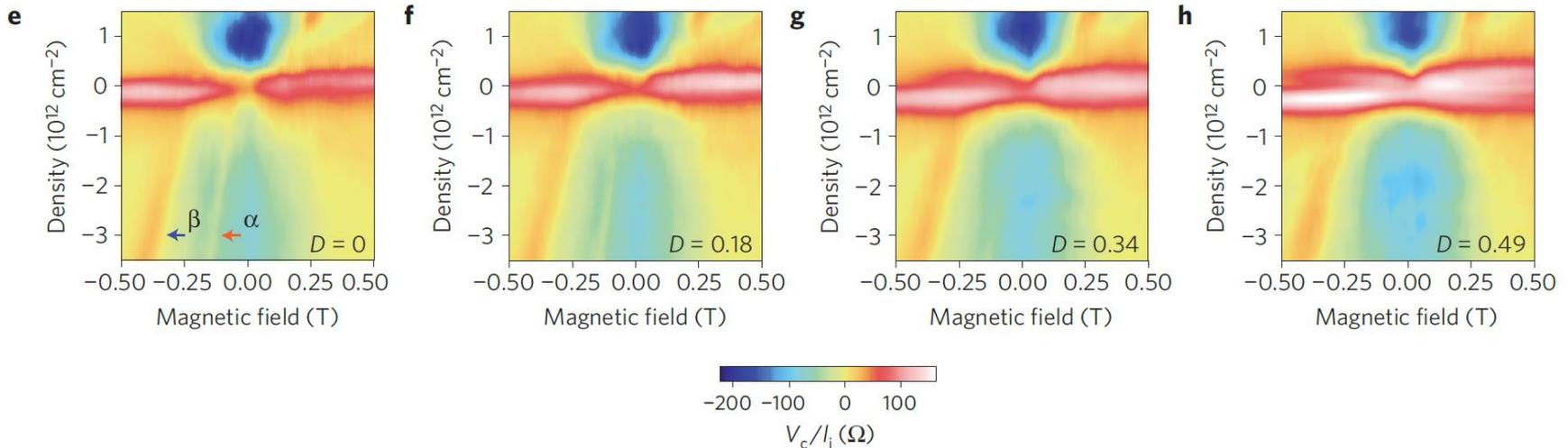


Enables the use of TMF as a probe of the change in the bandstructure

TMF as a ballistic electron spectroscopy method

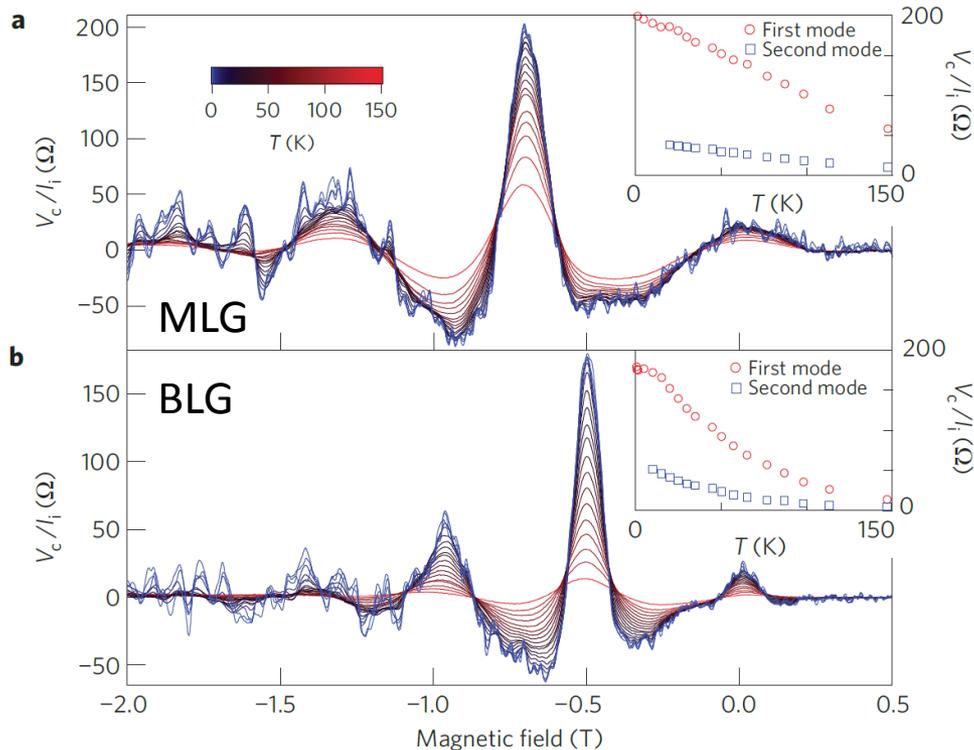


A finite D induces a potential difference between the layers
 → hybridization MLG-like and BLG-like subbands



As D increases the α -peak starts to shift downward and eventually disappears at low density

Temperature dependence of TMF spectra



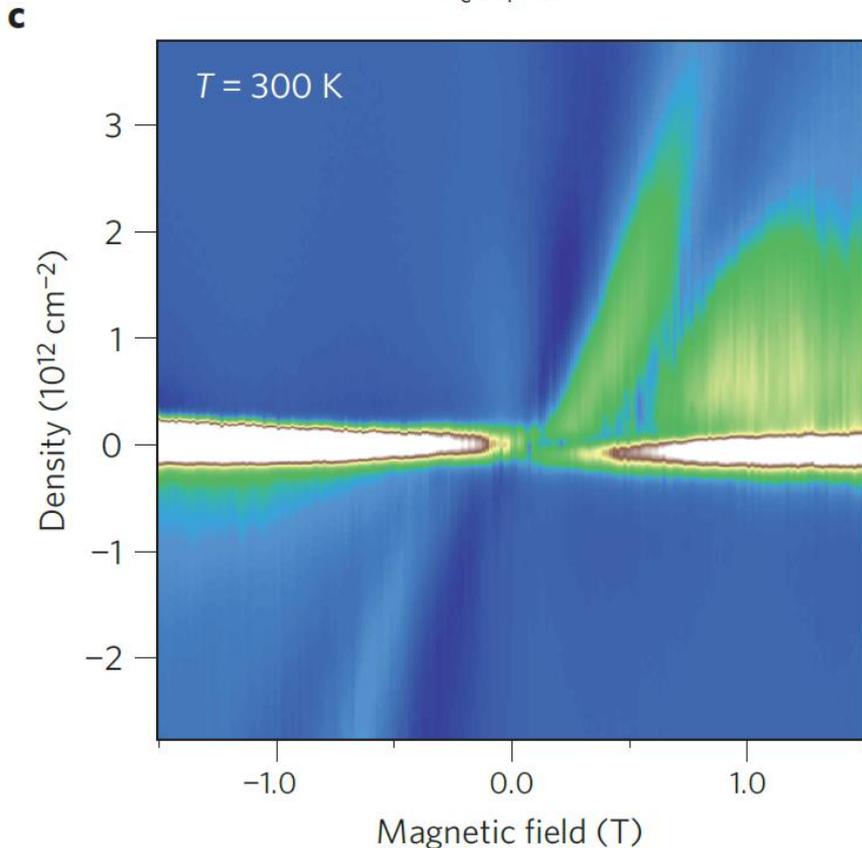
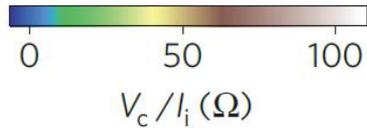
Two effects of temperature:

1. Increase in dephasing
2. Loss of ballistic transport due to new scattering channels

- Finestructure at low T due to interference between different paths travelling to the collector
- If broadening of k_F is on the order of $1/L$ the interference is washed out
- Should appear at $T = 15$ K

- Decreasing focusing peak amplitudes with T (linear for MLG and saturating for BLG)
- A potential scattering mechanism includes longitudinal acoustic phonons which give rise to a linear T-dependence of the scattering rate
- More theoretical work is needed to understand the temperature dependence!

Remarkable robustness of TMF in graphene



- First mode clearly visible indicating room-T ballistic transport well into the μ -regime
- T three times higher than in semiconductor heterostructures
- Lack of remote interfacial phonon scattering from hBN

Summary

- Observation of TMF in MLG, BLG and TLG
 - The use of TMF as a ballistic electron spectroscopy method to investigate controlled changes in the electronic structure
 - TMF in graphene survives up to 300 K
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Conclusions

- Could we design an experiment to study the edge quality of H-plasma defined edges by TMF?

Thank you for your attention!